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July 2012

# FAN7393A Half-Bridge Gate Drive IC

#### **Features**

- Floating Channel for Bootstrap Operation to +600V
- Typically 2.5A/2.5A Sourcing/Sinking Current Driving Capability
- Extended Allowable Negative V<sub>S</sub> Swing to -9.8V for Signal Propagation at V<sub>BS</sub>=15V
- High-Side Output in Phase of IN Input Signal
- 3.3V and 5V Input Logic Compatible
- Matched Propagation Delay for Both Channels
- Built-in Shutdown Function
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Cancelling Circuit
- Internal 400ns Minimum Dead Time at R<sub>DT</sub>=0Ω
- Programmable Turn-On Delay Control (Dead-Time)

### **Applications**

- High-Speed Power MOSFET and IGBT Gate Driver
- Induction Heating
- High-Power DC-DC Converter
- Synchronous Step-Down Converter
- Motor Drive Inverter

#### Description

The FAN7393A is a half-bridge gate-drive IC with shutdown and programmable dead-time control functions that can drive high-speed MOSFETs and Isolated Gate Bridge Transistors (IGBTs) operating up to +600V. It has a buffered output stage with all NMOS transistors designed for high-pulse-current driving capability and minimum cross-conduction.

Fairchild's high-voltage process and common-mode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circumstances. An advanced level-shift circuit offers high-side gate driver operation up to  $V_S$ =-9.8V (typical) for  $V_{BS}$ =15V.

The UVLO circuit prevents malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

The high-current and low-output voltage drop feature makes this device suitable for diverse half- and full-bridge inverters; motor drive inverters, switching mode power supplies, induction heating, and high-power DC-DC converter applications.

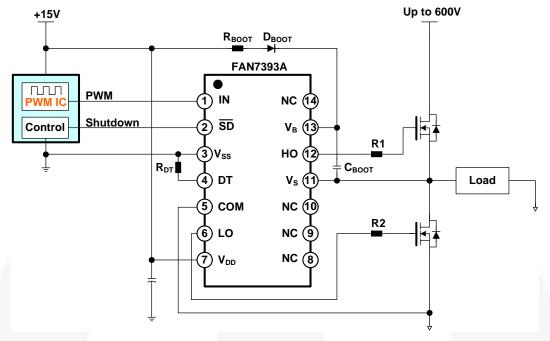
14-SOP



### **Ordering Information**

Part Number	Package	Operating Temperature	Packing Method
FAN7393AMX	14-SOIC	-40°C to +125°C	Tape & Reel

### **Typical Application Diagrams**



**Figure 1. Typical Application Circuit** 

### **Internal Block Diagram**

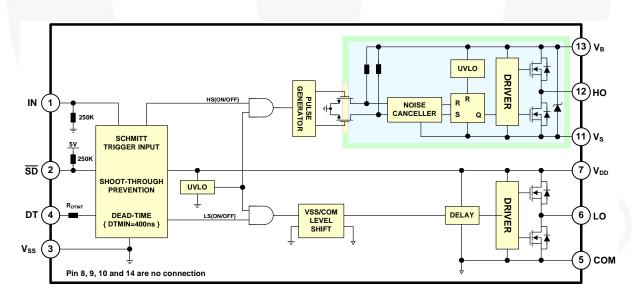


Figure 2. Functional Block Diagram

## **Pin Configuration**

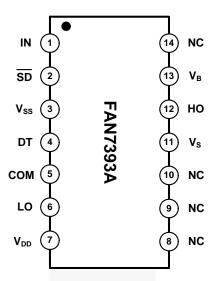


Figure 3. Pin Configurations (Top View)

### **Pin Definitions**

Pin#	Name	Description
1	IN	Logic Input for High-Side and Low-Side Gate Driver Output, In-Phase with HO
2	SD	Logic Input for Shutdown
3	V <sub>SS</sub>	Logic Ground
4	DT	Dead-Time Control with External Resistor (Referenced to V <sub>SS</sub> )
5	COM	Ground
6	LO	Low-Side Driver Return
7	V <sub>DD</sub>	Supply Voltage
8	NC	No Connection
9	NC	No Connection
10	NC	No Connection
11	V <sub>S</sub>	High-Voltage Floating Supply Return
12	НО	High-Side Driver Output
13	V <sub>B</sub>	High-Side Floating Supply
14	NC	No Connection

### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}C$  unless otherwise specified.

Symbol	Characteristics	Min.	Max.	Unit
V <sub>B</sub>	High-Side Floating Supply Voltage	-0.3	625.0	V
Vs	High-Side Floating Offset Voltage <sup>(1)</sup>	V <sub>B</sub> -V <sub>SHUNT</sub>	V <sub>B</sub> +0.3	V
V <sub>HO</sub>	High-Side Floating Output Voltage	V <sub>S</sub> -0.3	V <sub>B</sub> +0.3	V
$V_{LO}$	Low-Side Output Voltage	-0.3	V <sub>DD</sub> +0.3	V
$V_{DD}$	Low-Side and Logic Fixed Supply Voltage	-0.3	25.0	V
V <sub>IN</sub>	Logic Input Voltage (IN)	-0.3	V <sub>DD</sub> +0.3	V
V <sub>SD</sub>	Logic Input Voltage (SD)	V <sub>SS</sub>	5.5	V
DT	Programmable Dead-Time Pin Voltage	-0.3	V <sub>DD</sub> +0.3	V
V <sub>SS</sub>	Logic Ground	V <sub>DD</sub> -25	V <sub>DD</sub> +0.3	V
dV <sub>S</sub> /dt	Allowable Offset Voltage Slew Rate		± 50	V/ns
P <sub>D</sub>	Power Dissipation <sup>(2, 3, 4)</sup>		1	W
$\theta_{JA}$	Thermal Resistance		110	°C/W
TJ	Junction Temperature		+150	°C
T <sub>STG</sub>	Storage Temperature	-55	+150	°C

#### Notes:

- This IC contains a shunt regulator on V<sub>BS</sub>. This supply pin should not be driven by a low-impedance voltage source greater than V<sub>SHUNT</sub> specified in the Electrical Characteristics section.
- 2. Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- Refer to the following standards: JESD51-2: Integral circuits thermal test method environmental conditions - natural convection, and JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
- 4. Do not exceed maximum P<sub>D</sub> under any circumstances.

### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>B</sub>	High-Side Floating Supply Voltage	V <sub>S</sub> +10	V <sub>S</sub> +20	V
V <sub>S</sub>	High-Side Floating Supply Offset Voltage	6-V <sub>DD</sub>	600	V
V <sub>HO</sub>	High-Side Output Voltage	V <sub>S</sub>	V <sub>B</sub>	V
$V_{DD}$	Low-Side and Logic Fixed Supply Voltage	10	20	V
$V_{LO}$	Low-Side Output Voltage	COM	V <sub>DD</sub>	V
V <sub>IN</sub>	Logic Input Voltage (IN)	$V_{SS}$	V <sub>DD</sub>	V
V <sub>SD</sub>	Logic Input Voltage (SD)	V <sub>SS</sub>	5	V
DT	Programmable Dead-Time Pin Voltage	V <sub>SS</sub>	V <sub>DD</sub>	V
V <sub>SS</sub>	Logic Ground	-5	+5	V
T <sub>A</sub>	Operating Ambient Temperature	-40	+125	°C

#### **Electrical Characteristics**

 $V_{BIAS}(V_{DD},\ V_{BS})$ =15.0V,  $V_{SS}$ =COM=0V, DT= $V_{SS}$ , and  $T_A$ =25°C unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$ /COM and are applicable to the respective input leads: IN and SD. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Characteristics	Test Condition	Min.	Тур.	Max.	Unit
POWER S	SUPPLY SECTION			u .		1
$I_{QDD}$	Quiescent V <sub>DD</sub> Supply Current	V <sub>IN</sub> =0V or 5V		600	1000	μΑ
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	V <sub>IN</sub> =0V or 5V		55	100	μΑ
I <sub>PDD</sub>	Operating V <sub>DD</sub> Supply Current	f <sub>IN</sub> =20KHz, No Load		1.0	1.6	mA
I <sub>PBS</sub>	Operating V <sub>BS</sub> Supply Current	C <sub>L</sub> =1nF, f <sub>IN</sub> =20KHz, RMS		450	800	μΑ
I <sub>SD</sub>	Shutdown Mode Supply Current	SD=V <sub>SS</sub>		650	1000	μΑ
I <sub>LK</sub>	Offset Supply Leakage Current	V <sub>B</sub> =V <sub>S</sub> =600V			10	μΑ
BOOTST	RAPPED SUPPLY SECTION					I
V <sub>DDUV+</sub> V <sub>BSUV+</sub>	V <sub>DD</sub> and V <sub>BS</sub> Supply Under-Voltage Positive-Going Threshold Voltage	V <sub>IN</sub> =0V, V <sub>DD</sub> =V <sub>BS</sub> =Sweep	7.8	8.8	9.8	V
V <sub>DDUV</sub> - V <sub>BSUV</sub> -	V <sub>DD</sub> and V <sub>BS</sub> Supply Under-Voltage Negative-Going Threshold Voltage	V <sub>IN</sub> =0V, V <sub>DD</sub> =V <sub>BS</sub> =Sweep	7.3	8.3	9.3	V
V <sub>DDUVH</sub> - V <sub>BSUVH</sub>	V <sub>DD</sub> and V <sub>BS</sub> Supply Under-Voltage Lockout Hysteresis Voltage	V <sub>IN</sub> =0V, V <sub>DD</sub> =V <sub>BS</sub> =Sweep		0.5		V
SHUNT R	EGULATOR SECTION					
$V_{SHUNT}$	Shunt Regulator Clamping Voltage for $V_{\rm BS}$	V <sub>BS</sub> =Sweep, I <sub>SHUNT</sub> =5mA	21	23	25	V
INPUT LC	OGIC SECTION					
V <sub>IH</sub>	Logic "1" Input Voltage for HO & Logic "0" for LO		2.5			V
$V_{IL}$	Logic "0" Input Voltage for HO & Logic "1" for LO				8.0	V
I <sub>IN+</sub>	Logic Input High Bias Current	V <sub>IN</sub> =5V, SD=0V		20	50	μΑ
I <sub>IN-</sub>	Logic Input Low Bias Current	V <sub>IN</sub> =0V, SD=5V			3	μΑ
R <sub>IN</sub>	Logic Input Pull-Down Resistance		100	250		ΚΩ
V <sub>SDCLAMP</sub>	Shutdown (SD) Input Clamping Voltage <sup>(5)</sup>			5.0	5.5	V
SD+	Shutdown (SD) Input Positive-Going Threshold	9	2.5			V
SD-	Shutdown (SD) Input Negative-Going Threshold				0.8	V
$R_{PSD}$	Shutdown (SD) Input Pull-Up Resistance		100	250		ΚΩ
GATE DR	RIVER OUTPUT SECTION					
$V_{OH}$	High-Level Output Voltage ( $V_{BIAS}$ - $V_{O}$ )	No Load (I <sub>O</sub> =0A)			1.5	V
V <sub>OL</sub>	Low-Level Output Voltage	No Load (I <sub>O</sub> =0A)			100	mV
I <sub>O+</sub>	Output High, Short-Circuit Pulsed Current <sup>(5)</sup>	V <sub>HO</sub> =0V, V <sub>IN</sub> =5V, PW ≤10µs	2.0	2.5		Α
I <sub>O-</sub>	Output Low, Short-Circuit Pulsed Current <sup>(5)</sup>	V <sub>HO</sub> =15V, V <sub>IN</sub> =0V, PW ≤10µs	2.0	2.5		Α
V <sub>SS</sub> /COM	V <sub>SS</sub> -COM/COM-V <sub>SS</sub> Voltage Endurability <sup>(5)</sup>		-5.0		5.0	V
Vs	Allowable Negative $V_{\rm S}$ Pin Voltage for IN Signal Propagation to HO			-9.8	-7.0	V

#### Note:

5 These parameters are guaranteed by design.

### **Dynamic Electrical Characteristics**

 $V_{BIAS}(V_{DD},\,V_{BS}) = 15.0V,\,V_{SS} = COM = 0V,\,C_L = 1000pF,\,DT = V_{SS,}\,and\,T_A = 25^{\circ}C,\,unless\,otherwise\,specified.$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>ON</sub>	Turn-On Propagation Delay <sup>(6)</sup>	$V_S=0V$ , $R_{DT}=0\Omega$		530	730	ns
t <sub>OFF</sub>	Turn-Off Propagation Delay	V <sub>S</sub> =0V		130	250	ns
t <sub>SD</sub>	Shutdown Propagation Delay			140	210	ns
Mt <sub>ON</sub>	Delay Matching, HO and LO Turn-On			0	90	ns
Mt <sub>OFF</sub>	Delay Matching, HO and LO Turn-Off			0	40	ns
t <sub>R</sub>	Turn-On Rise Time	V <sub>S</sub> =0V		25	50	ns
t <sub>F</sub>	Turn-Off Fall Time	V <sub>S</sub> =0V		15	35	ns
DT	Dead Time: LO Turn-Off to HO Turn-On, HO Turn-Off to LO Turn-On	$R_{DT}=0\Omega$	300	400	500	ns
		R <sub>DT</sub> =200KΩ	4	5	6	μs
MDT	Dead-Time Matching= DT <sub>LO-HO</sub> - DT <sub>HO-LO</sub>	R <sub>DT</sub> =0Ω		0	40	ns
IVIDT		R <sub>DT</sub> =200KΩ		0	500	ns

#### Note:

6 The turn-on propagation delay includes dead time.

### **Typical Characteristics**

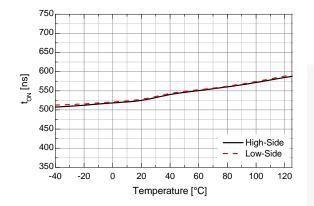


Figure 4. Turn-On Propagation Delay vs. Temperature

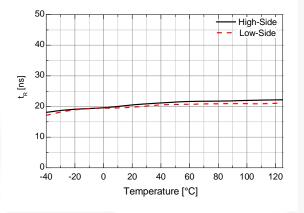


Figure 6. Turn-On Rise Time vs. Temperature

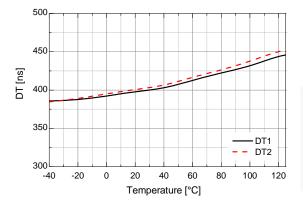


Figure 8. Dead Time ( $R_{DT}$ =0 $\Omega$ ) vs. Temperature

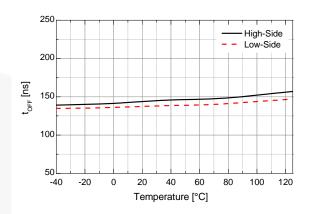


Figure 5. Turn-Off Propagation Delay vs. Temperature

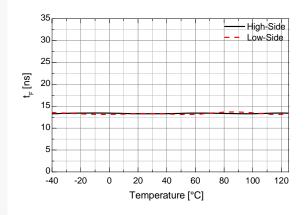


Figure 7. Turn-Off Fall Time vs. Temperature

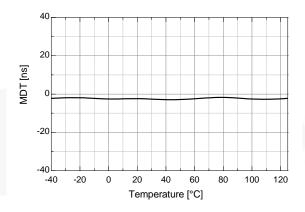


Figure 9. Dead Time Matching ( $R_{DT}$ =0 $\Omega$ ) vs. Temperature

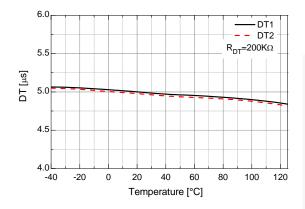


Figure 10. Dead Time ( $R_{DT}$ =200 $K\Omega$ ) vs. Temperature

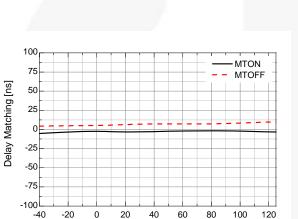


Figure 12. Delay Matching vs. Temperature

Temperature [°C]

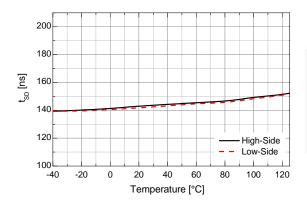


Figure 14. Shutdown Propagation Delay vs. Temperature

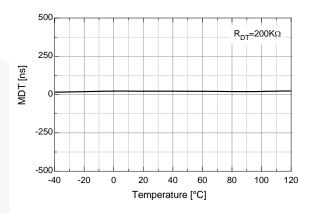


Figure 11. Dead-Time Matching ( $R_{DT}$ =200K $\Omega$ ) vs. Temperature

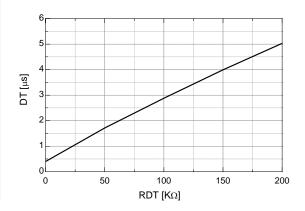


Figure 13. Dead Time vs. R<sub>DT</sub>

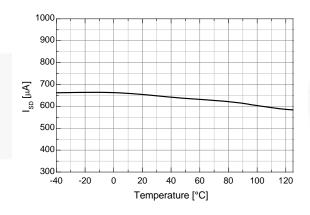


Figure 15. Shutdown Mode Supply Current vs. Temperature

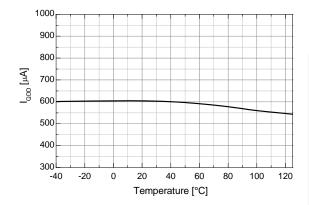


Figure 16. Quiescent V<sub>DD</sub> Supply Current vs. Temperature

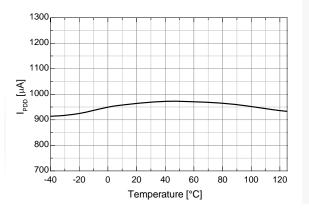


Figure 18. Operating V<sub>DD</sub> Supply Current vs. Temperature

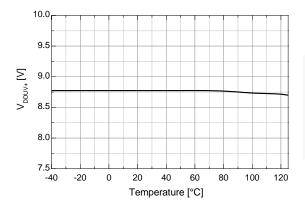


Figure 20. V<sub>DD</sub> UVLO+ vs. Temperature

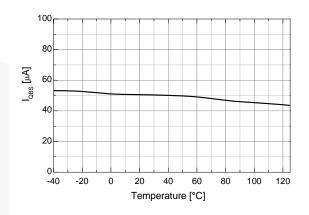


Figure 17. Quiescent V<sub>BS</sub> Supply Current vs. Temperature

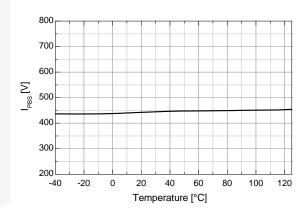


Figure 19. Operating V<sub>BS</sub> Supply Current vs. Temperature

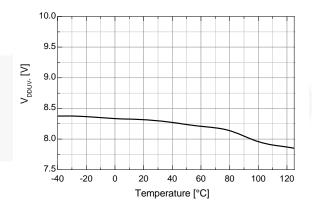


Figure 21. V<sub>DD</sub> UVLO- vs. Temperature

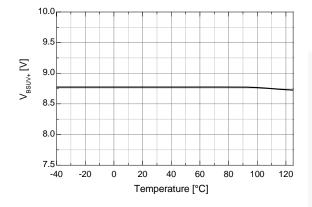


Figure 22. V<sub>BS</sub> UVLO+ vs. Temperature

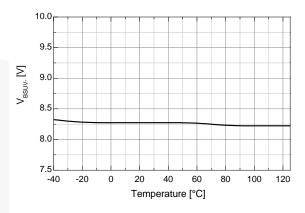


Figure 23. V<sub>BS</sub> UVLO- vs. Temperature

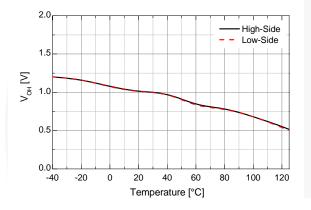


Figure 24. High-Level Output Voltage vs. Temperature

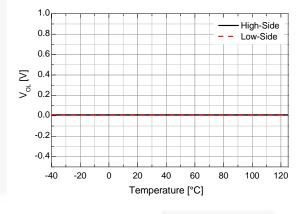


Figure 25. Low-Level Output Voltage vs. Temperature

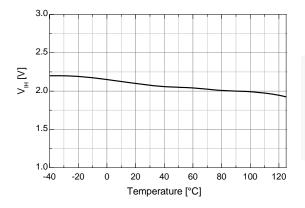


Figure 26. Logic HIGH Input Voltage vs. Temperature

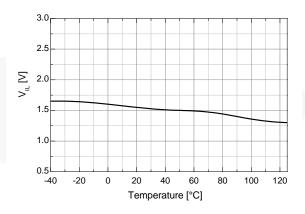


Figure 27. Logic LOW Input Voltage vs. Temperature

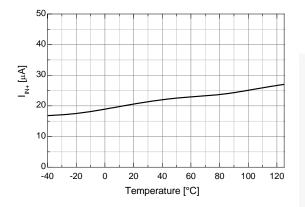


Figure 28. Logic Input High Bias Current vs. Temperature

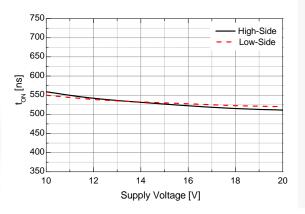


Figure 30. Turn-On Propagation Delay vs. Supply Voltage

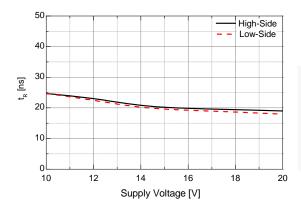


Figure 32. Turn-On Rise Time vs. Supply Voltage

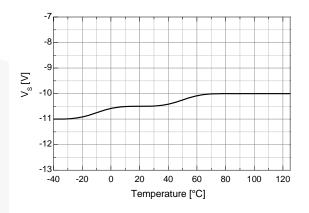


Figure 29. Allowable Negative V<sub>S</sub> Voltage vs. Temperature

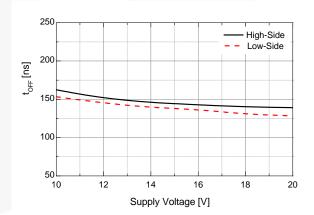


Figure 31. Turn-Off Propagation Delay vs. Supply Voltage

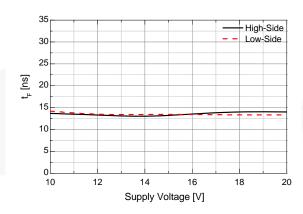


Figure 33. Turn-Off Fall Time vs. Supply Voltage

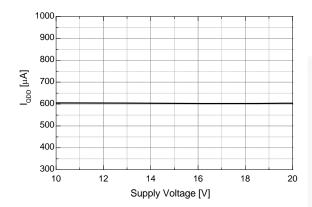


Figure 34. Quiescent V<sub>DD</sub> Supply Current vs. Supply Voltage

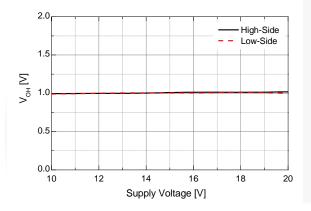


Figure 36. High-Level Output Voltage vs. Supply Voltage

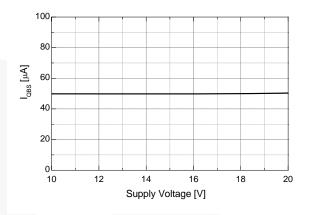


Figure 35. Quiescent V<sub>BS</sub> Supply Current vs. Supply Voltage

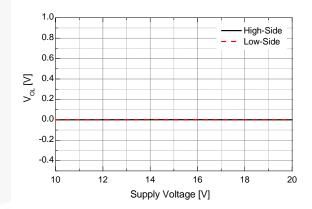


Figure 37. Low-Level Output Voltage vs. Supply Voltage

### **Switching Time Definitions**

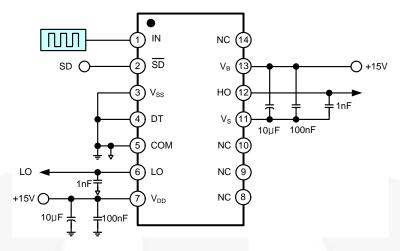


Figure 38. Switching Time Test Circuit

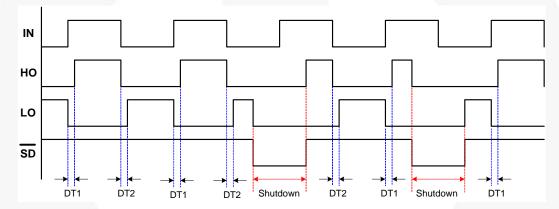


Figure 39. Input / Output Timing Diagram

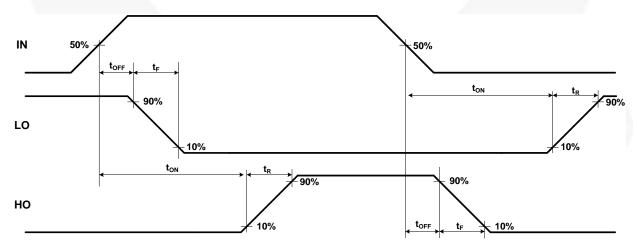


Figure 40. Switching Time Waveform Definition

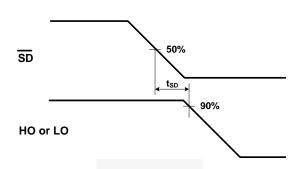


Figure 41. Shutdown Waveform Definition

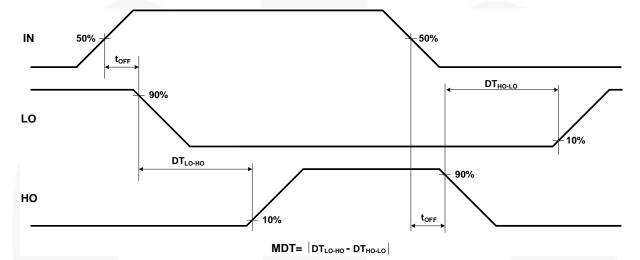


Figure 42. Dead-Time Waveform Definition

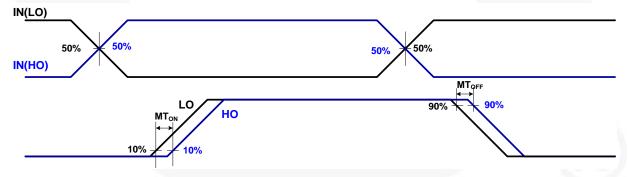
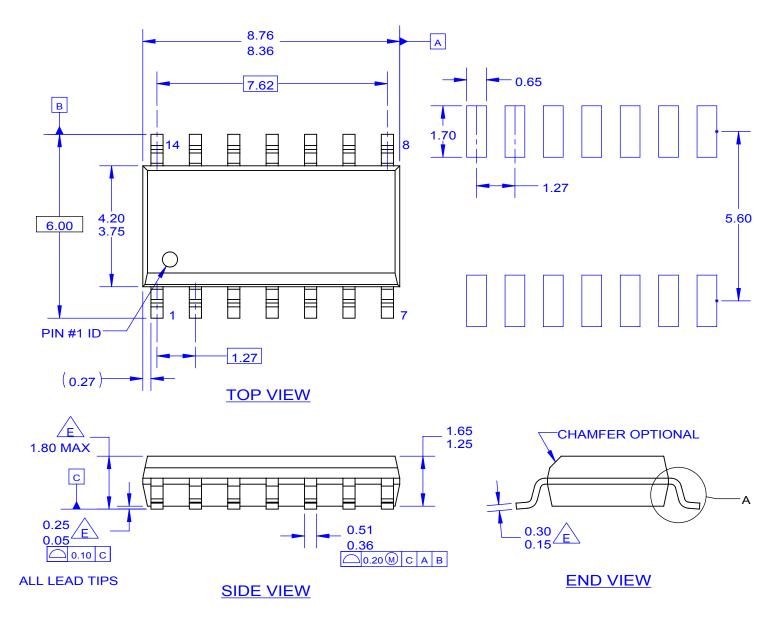
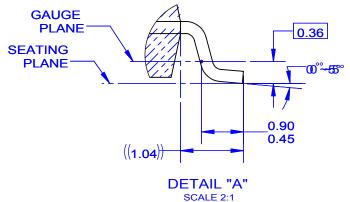


Figure 43. Delay Matching Waveform Definition



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